

# **PSMN013-100ES**

## N-channel 100V 13.9m $\Omega$ standard level MOSFET in I2PAK.

Rev. 3 — 29 September 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Standard level N-channel enhancement MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Table 1.	Quick reference da	TU .					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	100	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	68	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{ constant}}$		-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	[2]	-	11	13.9	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 50 V; see <u>Figure 14</u> ; see <u>Figure 13</u>		-	17	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 50 \text{ V}; \text{see } \frac{\text{Figure } 13}{\text{Figure } 14};$ see $\frac{\text{Figure } 14}{\text{Figure } 14}$	-	59	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 68 \text{ A}; V_{sup} \le 100 \text{ V};$ unclamped; $R_{GS} = 50 \Omega$	-	-	127	mJ

- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

### 2. Pinning information

Table 2. Pinning information

1 G gate 2 D drain 3 S source mb D mounting base; connected to drain	Pin	Symbol	Description	Simplified outline	Graphic symbol
2 D drain 3 S source mb D mounting base; connected to drain	1	G	gate		_
mb D mounting base; connected to drain	2	D	drain	mb	D
mb D mounting base; connected to drain	3	S	source		
SOT226 (I2PAK)	mb	D	mounting base; connected to drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN013-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226		

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	47	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{see } \frac{\text{Figure 1}}{Mode of the second o$	<u>[1]</u>	-	68	Α
$I_{DM}$	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	170	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	68	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$		-	272	Α
Avalanche ru	ıggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 68 A; $V_{sup}$ ≤ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	127	mJ

#### [1] Continuous current is limited by package.

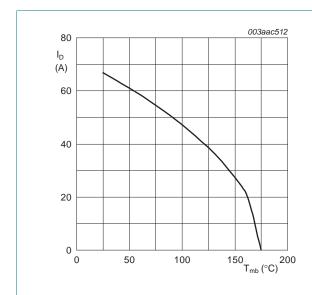


Fig 1. Continuous drain current as a function of mounting base temperature

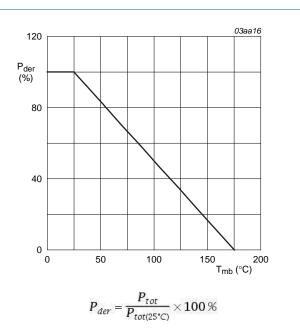


Fig 2. Normalized total power dissipation as a function of mounting base temperature

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 3	-	0.5	0.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

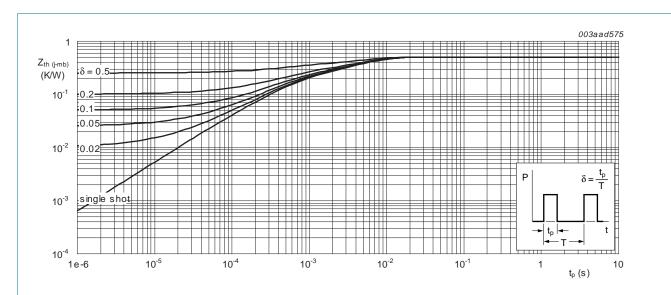


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions	ı	Min	Тур	Max	Unit
Static cha	racteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	(	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 9	,	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10; see Figure 9	:	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10		-	-	4.8	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$		-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	0.06	2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 11		-	30	38.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 11		-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 11	<u>[1]</u> .	-	11	13.9	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic (	characteristics						
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 13; see Figure 14		-	59	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		-	47.6	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 13; see Figure 14		-	13.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14		-	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge			-	4.6	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 13		-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 13</u>		-	4.4	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	3195	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25  ^{\circ}\text{C}$ ; see Figure 15		-	221	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	136	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$		-	20.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 \text{ °C}$		-	25	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	52.5	-	ns
t <sub>f</sub>	fall time			_	24	_	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Source-dra	Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 16	-	0.8	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	52	-	ns	
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	109	-	nC	

#### [1] Measured 3 mm from package.

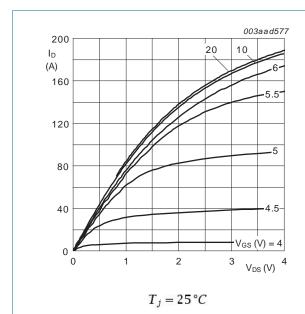


Fig 4. Output characteristics: drain current as a function of drain-source voltage; typical values

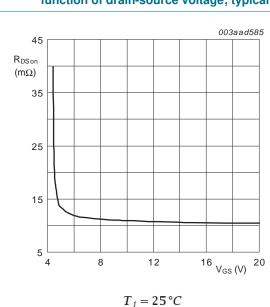


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

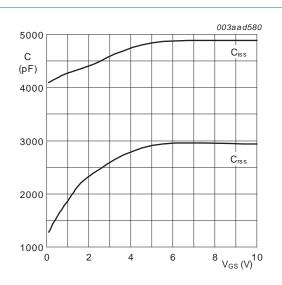


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$ 

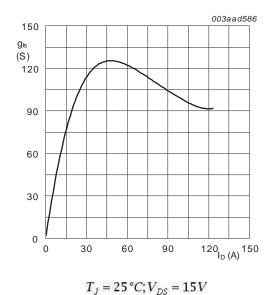


Fig 7. Forward transconductance as a function of drain current; typical values

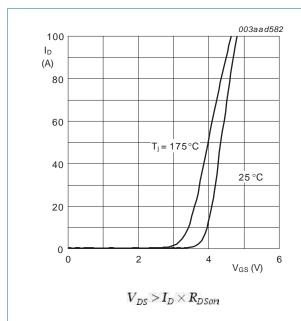


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

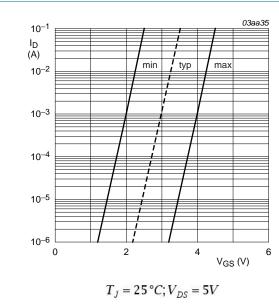


Fig 10. Sub-threshold drain current as a function of gate-source voltage

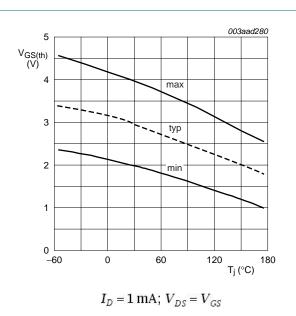


Fig 9. Gate-source threshold voltage as a function of junction temperature

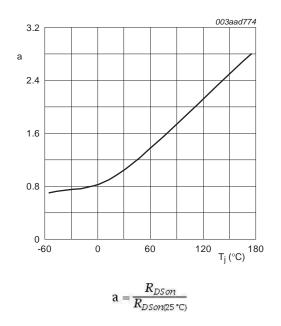


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

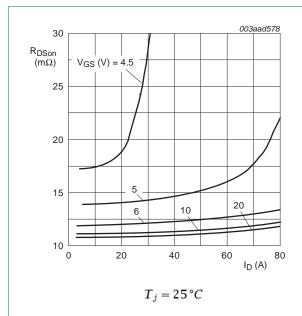


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

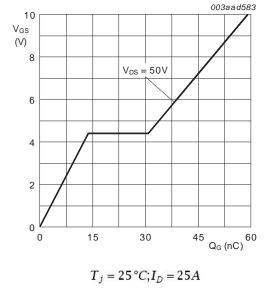


Fig 13. Gate-source voltage as a function of gate charge; typical values

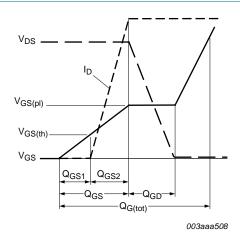


Fig 14. Gate charge waveform definitions

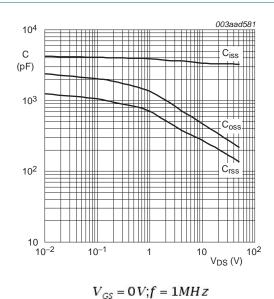


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

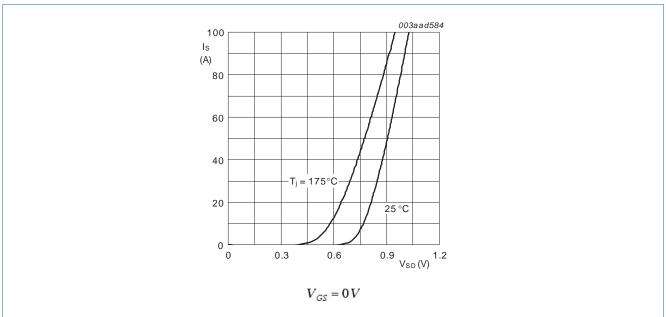


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline

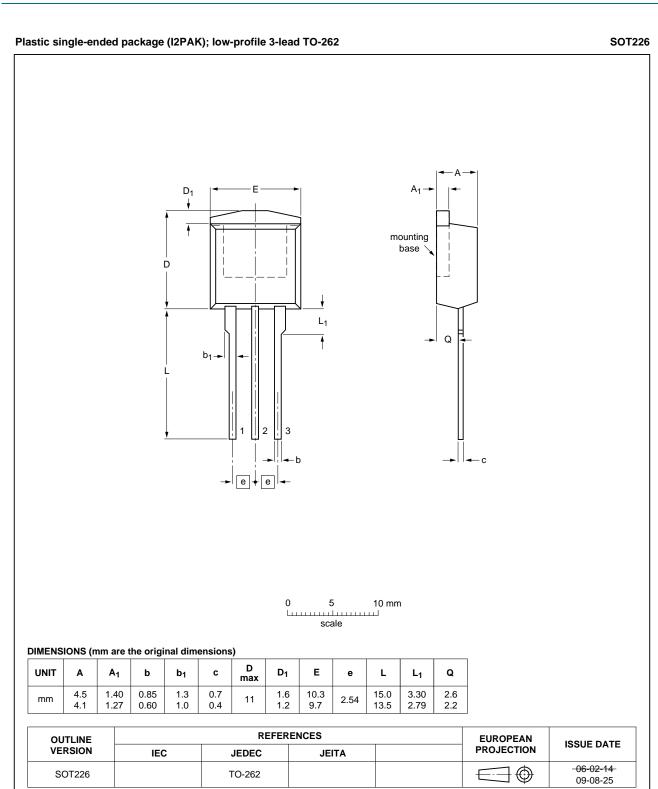


Fig 17. Package outline SOT226 (I2PAK)

## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-100ES v.3	20110929	Product data sheet	-	PSMN013-100ES v.2
Modifications:	<ul><li>Status changed fr</li><li>Various changes</li></ul>	om objective to product. to content.		
PSMN013-100ES v.2	20100219	Objective data sheet	-	PSMN013-100ES v.1

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN013-100ES

## **PSMN013-100ES**

#### N-channel 100V 13.9mΩ standard level MOSFET in I2PAK.

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# **PSMN013-100ES**

N-channel 100V 13.9m $\Omega$  standard level MOSFET in I2PAK.

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